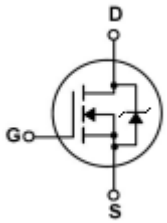
TO-247 N N-CHANNEL MOSFET in a TO-247 Plastic Package.

Low gate charge minimize switching loss and fast recovery body diode.HF Product.

DC/DC UPS
These devices are well suited for high efficiency switching DC/DC converters,Synchronous rectification and UPS inverter.





PIN1 G PIN 2 D PIN 3 S

S

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain Current	I_D(Tc=25)	120	A
	I_D(Tc=100)	88	A
Pulsed Drain Current	I_{DM}	480	A
Gate-Source Voltage	V_{GSS}	±20	V
Avalanche Current	I_{AR}	76.7	A
Avalanche energy L=0.5mH	E_{AS}	1200	mJ
Total Power Dissipation	P_D(Tc=25)	300	W
Junction and Storage Temperature Range	T_J,T_{STG}	-55 to 175	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

/ Electrical Characteristic Curve

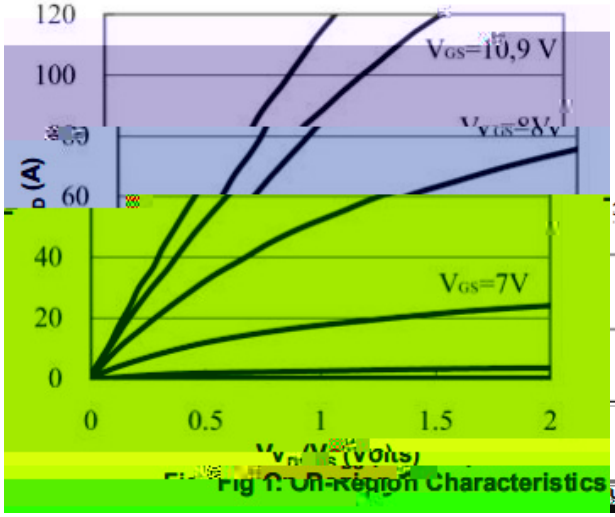
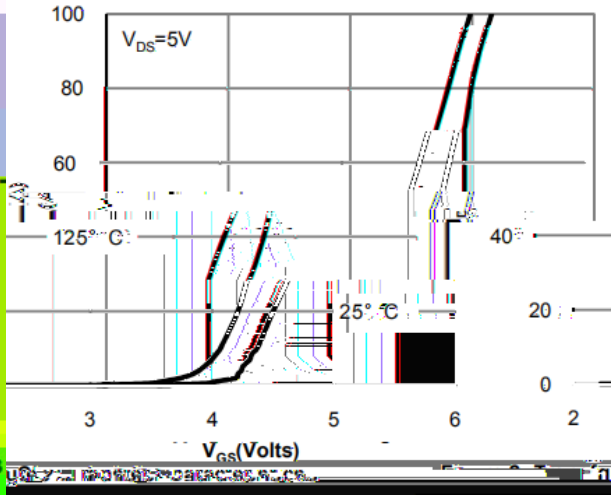
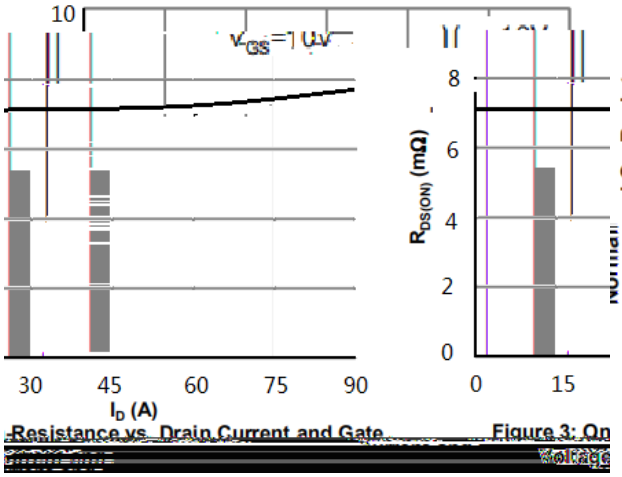


Fig 1: On-Region Characteristics





Resistance vs. Drain Current and Gate Figure 3: On Voltage

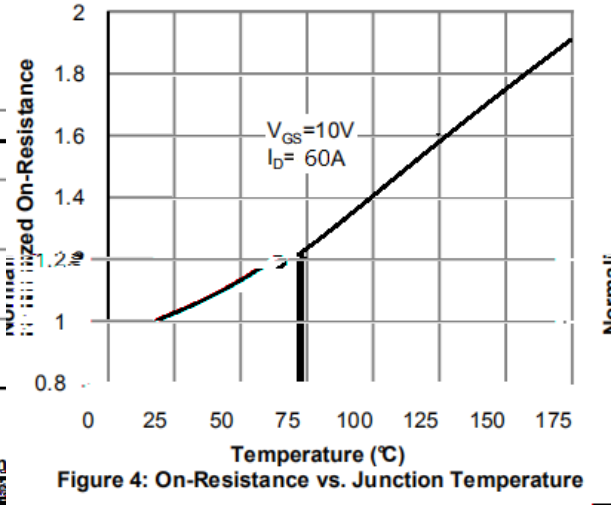
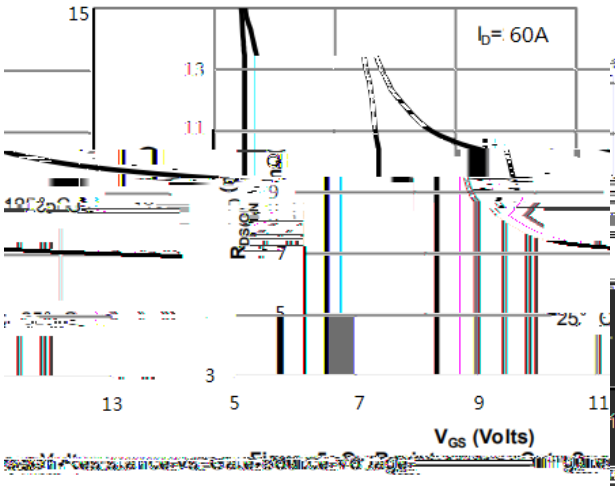
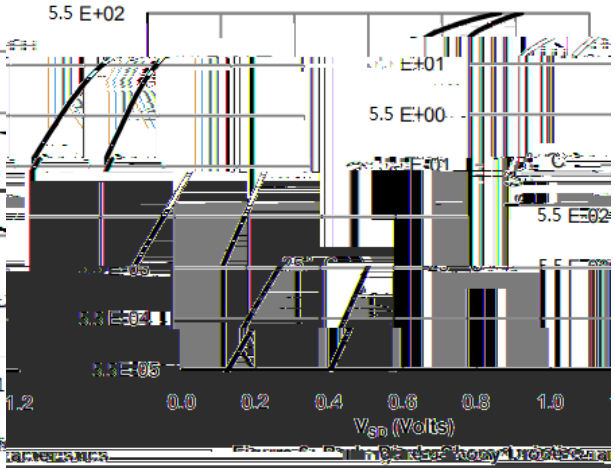
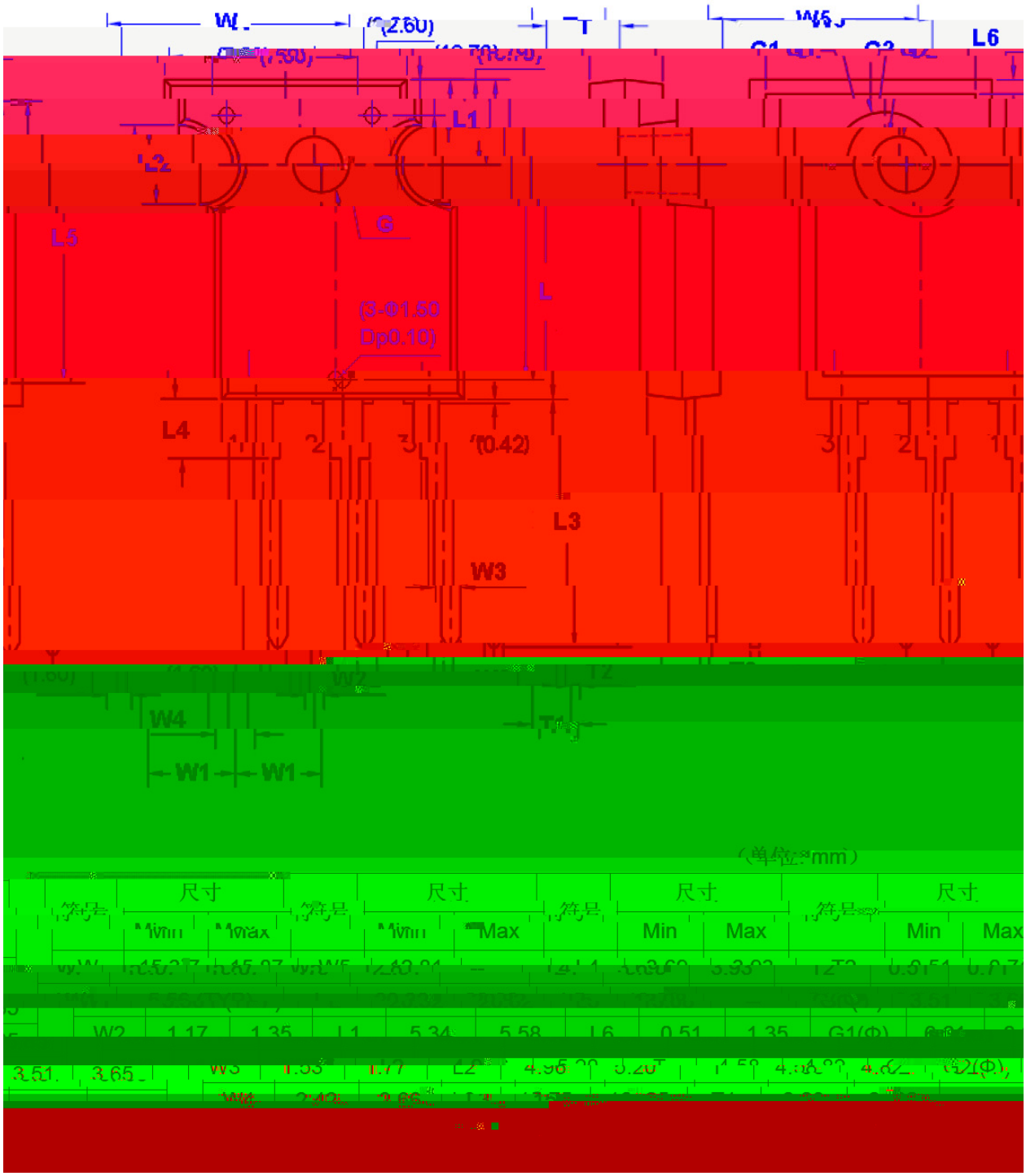


Figure 4: On-Resistance vs. Junction Temperature

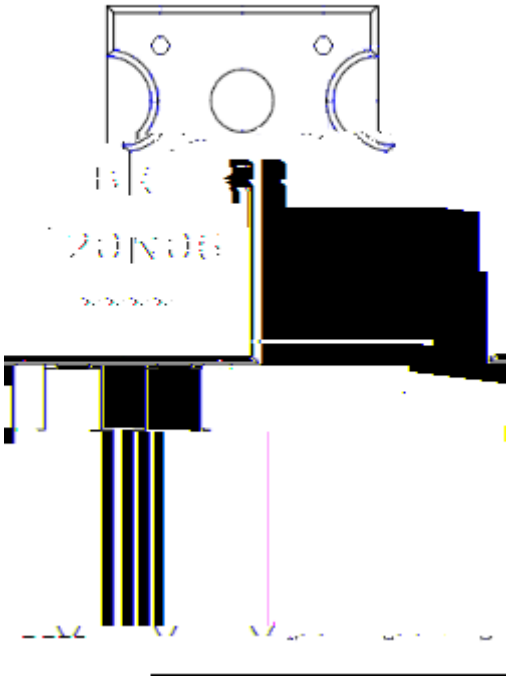




/ Package Dimensions



/ Marking Instructions



BR

120N06

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Note:

BR:

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3			2	10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec